),,			O(1). C. (1)			2814	
Man &						Attorney Docket No: MICR131.02	
Appleation Serial Number: 09/503638		Filing Date: 2/14/2000		Examiner: G. Peralta		Group Art Unit: 2814	
Invention: RA	NDOM ACCESS	MEMOR	Y				
	MISSIONER OF P ewith is an amend			·	The fee has be	en calculated as	
		С	LAIMS AS AMI	ENDED			
	CLAIMS REMAINING AFTER AMENDMENT		HIGHEST NUMBER PREVIOUSLY PAID FOR	NO. OF EXTRA CLAIMS PRESENT	RATE	ADDITIONAL FEE	
TOTAL CLAIMS	11	MINUS	20	0	\$18	\$ 0.00,	
INDEP. CLAIMS	6	MINUS	5	1	\$84	\$ 84.00	
	is hereby made under to and through one month (two months	<u>3/7/2002,</u> (\$110)	, comprising an e		shortened state	he Office Action of atomy period of:	
	TC	OTAL AD	DITIONAL FEE	FOR THIS AN	MENDMENT	\$1,004.00	
Small entity status of this application under 37 CFR 1.9 and 1.27 has been established by a verified statement previously submitted.							
A	A verified statement to establish small entity status under 37 CFR 1.9 and 1.27 is enclosed.						
<u>X</u> A	A check in the amount of \$\\\ 1004.00\ \] is attached.						
	Charge \$ to Deposit Account						
· · · · · · · · · · · · · · · · · · ·	To additional fee is	required.		A	1		
Γ	Pate / / 4	no	Steven R. Ormis	ston			

I hereby certify that this correspondence and all correspondence identified as accompanying this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to the Assistant Commissioner for Patents, Washington, D.C. 20231 on 3772002.

Reg. No. 35974

ORIGINALLY FILED

In re Application of:

Kirk D. Prall, et al.

Serial No: 09/503,638

Filed: -February 14, 2000-

For: RANDOM ACCESS MEMORY Attorney

TECHNOLOGY CENTER 200 Docket Number: MICR131.02

Group Art Unit: 2814

Examiner: G. Peralta

March 5, 2002

Assistant Commissioner of Patents Washington, DC 20231

Sir:

RESPONSE TO THE OFFICE ACTION MAILED SEPTEMBER 7, 2001

Please amend the Application as follows.

In The Claims

Add the following new claims.

A semiconductor memory device, comprising: 30.(new)

a substrate;

a contact region in the substrate;

a first dopant implant in the contact region, the first implant defining a first implant profile; and

a second dopant implant in the contact region, the second implant defining a second implant profile narrower and deeper than the first implant profile.

A device according to Claim 30, wherein the first and second 31.(new) dopants have the same conductivity type.

A device according to Claim 31, further comprising a capacitor in 32.(new) electrical contact with the contact region.

03/20/2002 SMINASSI 00000012 09503638